



PTO/SB/08A (Substitute for form 1449/PTO)		Attorney Docket No.: 023-0029
		Application No.: 10/729,865
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		First Named Inventor: En-Hsing Chen, et al.
		Filing Date: December 5, 2003
		Group Art Unit: 2824
		Examiner Name: Nguyen, Van Thu T.
Sheet 1 of 2		Date Submitted: December 7, 2005

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Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
VTN	AA	5,299,166	03-29-1994	Suh et al.		
	AB	6,115,287	09-05-2000	Shimizu et al.		
	AC	6,295,227 B1	09-25-2001	Sakui et al.		
	AD	6,512,694 B2	01-28-2003	Herd		
	AE	6,522,583 B2	02-18-2003	Kanda et al.		
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	AH	6,859,395 B2	02-22-2005	Matsunaga et al.		
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VTN	AM	6,567,287 B2	05-20-2003	Scheuerlein		
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VTN	AN	WO-2002-43067 US	05-2002			
Examiner Signature <i>Van Thu T. Nguyen</i>			Date Considered		0/6/05	

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¹Applicant's unique citation designation number (optional).

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³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3)

⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document.

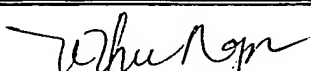
⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible.

⁶Applicant is to place a check mark here if English language Translation is attached.

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NON PATENT LITERATURE DOCUMENTS

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VTN	AA	KIM ET AL. "Scaled SONOSFET NAND Flash EEPROM; The NAND Type Flash EEPROM using the Scaled SONOSFET", Transcripts KIEE, Vol. 49C, No. 1, January 2000, pp. 1-7.	Abstract only
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VTN	AC	NAJI, PETER K. ET AL., "A 256kb 3.0V 1T1MTJ Nonvolatile Magnetoresistive RAM," 2001 IEEE ISSCC, February 6, 2001, Paper 7.6, and corresponding presentation slides (35 pages).	
Examiner Signature			Date Considered 1/6/06

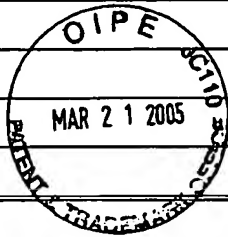
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VTN	AM	5,703,382	12-30-1997	Hack et al.		
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VTN	AN	JA 62-142363	06-25-1987			
	AO	JA 62-155568	07-10-1987			
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VTN	AQ	JA-2002-280467	09-27-2002			
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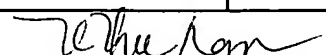
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VTN	AR	5,715,194	02-03-1998	Hu	
	AS	5,751,012	05-12-1998	Wolstenholme et al.	
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	AZ	5,978,265	11-02-1999	Kirisawa et al.	
	BA	6,034,882	03-07-2000	Johnson et al.	
	BB	6,055,180	04-25-2000	Gudesen et al.	
	BC	6,107,658	08-22-2000	Itoh et al.	
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	BE					
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	BH					
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NTN	BI	6,188,611 B1	02-13-2001	Endoh et al.	
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	BS	6,490,194	12-03-2002	Hoenigschmid	
	BT	6,498,747	12-24-2002	Gogl et al.	
NTN	BU	6,512,703 B2	01-28-2003	Sakui et al.	

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	BV					
	BW					
	BX					
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VTN	BZ	6,515,888	02-04-2003	Johnson et al.	
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	CO					
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NTN	CQ	US-2002/0021587 A1	02-21-2002	Sakui et al.	
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	CY	US-6,049,494	04-2000	Sakui et al.	
	CZ	US-5,991,202	11-1999	Derhacopian et al.	
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	DD					
	DE					
	DF					
	DG					
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VTN	AA	DURISETY, CHANDRA SEKHAR ACHARYULU, "Analysis and Characterization of Single-Poly Floating Gate Devices in 0.35um PDSOI Process", A Thesis Presented for the Master of Science Degree, The University of Tennessee, Knoxville, December 2002, pp. i-viii and 1-80.	
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NTN	AO	SHIN, JONGSHIN, ET AL., "A New Charge Pump Without Degradation in Threshold Voltage Due to Body Effect," IEEE Journal of Solid-State Circuits, Vol. 35, No. 8, August 2000, pp. 1227-1230.	
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NTN	AT	THEAN, AARON, ET AL., "Flash memory: towards single-electronics," IEEE Potentials, October/November 2002, pp. 35-41.	
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VTN	AA	4,646,266	24 Feb 1987	Ovshinsky et al.		
	AB	5,514,907	07 May 1996	Moshayedi		
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	AN					
	AP					
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)						
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	AS					
	AT					
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